NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRF314A** is Designed for Class C Power Amplifier Applications up to 200 MHz.

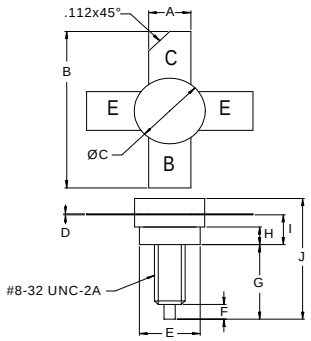
FEATURES:

- P_G = 10 dB min. at 30 W/ 150 MHz
- Withstands **30:1** Load VSWR
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	2.9 ^{O}C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10770

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 200 mA			35			V
BV_{CES}	I_C = 200 mA			65			V
BV_{EBO}	I_E = 10 mA			4.0			V
I_{CBO}	V_E = 28 V					2.0	mA
h_{FE}	V_{CE} = 5.0 V	I_C = 200 mA		5		---	---
C_{OB}	V_{CB} = 28 V		f = 1.0 MHz			50	pF
P_G	V_{CC} = 28 V	P_{OUT} = 30 W	f = 150 MHz	10	13.5		dB
η_C				50	60		%
ψ				30:1 minimum without degration in output power			

Specifications are subject to change without notice.